



# **MMDT5401**

# **DUAL PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR**

## **Features**

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMDT 5551)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)

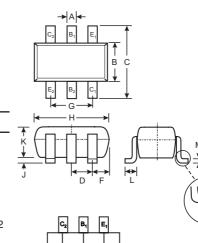
## **Mechanical Data**

• Case: SOT-363

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- Case Material: Molded Plastic. UL Flammability . Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C .
- Terminals: Solderable per MIL-STD-202, Method 208 .
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking (See Page 2): K4M
- Order & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)

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SOT-363							
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65 Nominal						
F	0.30	0.40					
н	1.80	2.20					
J	_	0.10					
к	0.90	1.00					
L	0.25 0.40						
м	0.10	0.25					
α	0°	8°					
All Dimensions in mm							

Maximum Ratings	@ $T_A = 25^{\circ}C$ unless otherwis	e specified	
Charac	teristic	Symbol	MMDT5401

Characteristic	Symbol	MMDT5401	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous (Note 1)	Ι <sub>C</sub>	-200	mA
Power Dissipation (Note 1, 2)	Pd	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>0JA</sub>	625	K/W
Operating and Storage and Temperature Range	Tj, T <sub>STG</sub>	-55 to +150	°C

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. Maximum combined dissipation.

3. No purposefully added lead.



#### **Electrical Characteristics** @ $T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Min	Мах	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)			1	1			
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-160		V	$I_{C} = -100 \mu A, I_{E} = 0$		
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-150		V	$I_{\rm C} = -1.0 {\rm mA}, I_{\rm B} = 0$		
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	—	V	$I_E = -10 \mu A, I_C = 0$		
Collector Cutoff Current	I <sub>CBO</sub>	_	-50	nA μA			
Emitter Cutoff Current	I <sub>EBO</sub>	_	-50	nA	$V_{EB} = -3.0V, I_{C} = 0$		
ON CHARACTERISTICS (Note 4)							
DC Current Gain	h <sub>FE</sub>	50 60 50	240 	_	$ \begin{array}{ll} I_C = & -1.0mA, \ V_{CE} = & -5.0V \\ I_C = & -10mA, \ V_{CE} = & -5.0V \\ I_C = & -50mA, \ V_{CE} = & -5.0V \end{array} $		
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.2 -0.5	V	$I_{C} = -10mA, I_{B} = -1.0mA$ $I_{C} = -50mA, I_{B} = -5.0mA$		
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		-1.0	V	$I_{C} = -10mA, I_{B} = -1.0mA$ $I_{C} = -50mA, I_{B} = -5.0mA$		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C <sub>obo</sub>	—	6.0	pF	$V_{CB} = -10V$ , f = 1.0MHz, I <sub>E</sub> = 0		
Small Signal Current Gain	h <sub>fe</sub>	40	200	_	$V_{CE} = -10V, I_C = -1.0mA, f = 1.0kHz$		
Current Gain-Bandwidth Product	fT	100	300	MHz	$V_{CE} = -10V, I_{C} = -10mA, f = 100MHz$		
Noise Figure	NF	_	8.0	dB	$\label{eq:Vce} \begin{array}{l} V_{CE}=-5.0V,\ I_C=-200\mu A,\\ R_S=10\Omega,\ f=1.0kHz \end{array}$		

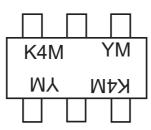
## Ordering Information (Note 5)

Device	Packaging	Shipping
MMDT5401-7-F	SOT-363	3000/Tape & Reel

Notes: 4. Short duration test pulse used to minimize self-heating effect.

5. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

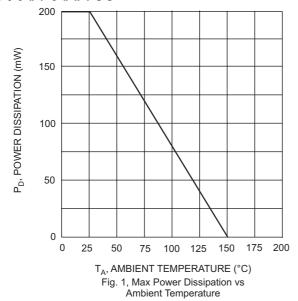


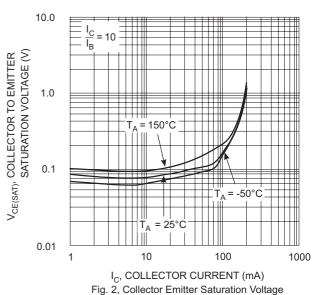
 $\begin{array}{l} \mathsf{K4M} = \mathsf{Product Type Marking Code} \\ \mathsf{YM} = \mathsf{Date Code Marking} \\ \mathsf{Y} = \mathsf{Year ex: N} = 2002 \\ \mathsf{M} = \mathsf{Month ex: 9} = \mathsf{September} \end{array}$ 

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W
Manath				-		-						
Month	Jan	Feb	March	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec







ig. 2, Collector Emitter Saturation Voltag vs. Collector Current

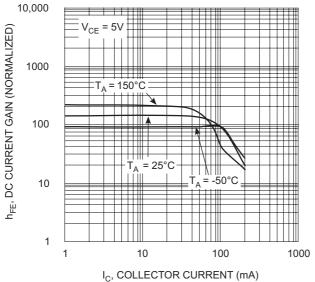
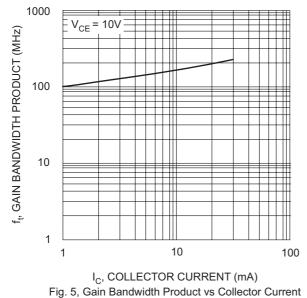


Fig. 3, DC Current Gain vs. Collector Current



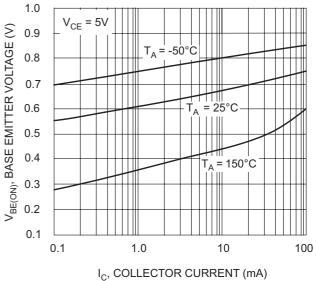


Fig. 4, Base Emitter Voltage vs. Collector Current



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